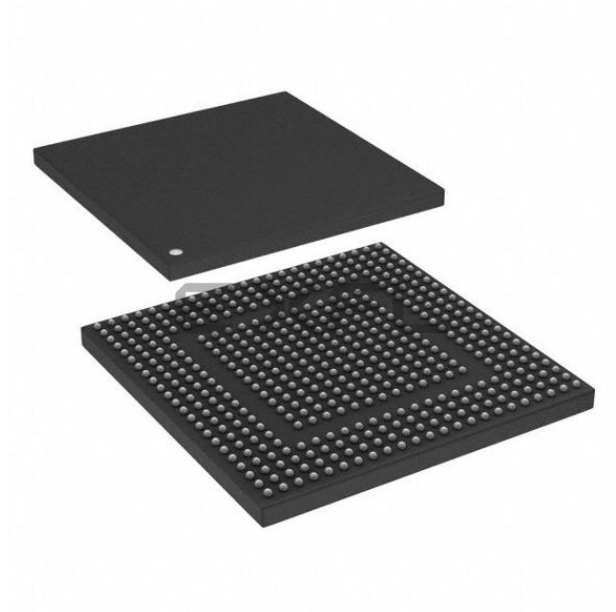

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Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	e200z7d
Core Size	32-Bit Dual-Core
Speed	180MHz
Connectivity	CANbus, EBI/EMI, Ethernet, FlexRay, I²C, LINbus, SPI
Peripherals	DMA, POR, PWM, WDT
Number of I/O	-
Program Memory Size	1.5MB (1.5M x 8)
Program Memory Type	FLASH
EEPROM Size	64K x 8
RAM Size	384K x 8
Voltage - Supply (Vcc/Vdd)	1.14V ~ 5.5V
Data Converters	A/D 34x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 105°C (TA)
Mounting Type	Surface Mount
Package / Case	473-LFBGA
Supplier Device Package	473-MAPBGA (19x19)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/spc5674kavms2

3.2 416-ball TEPBGA Pin Assignments

Figure 6 shows the 416-ball TEPBGA pin assignments in one figure. The same information is shown in Figure 7 through Figure 10.

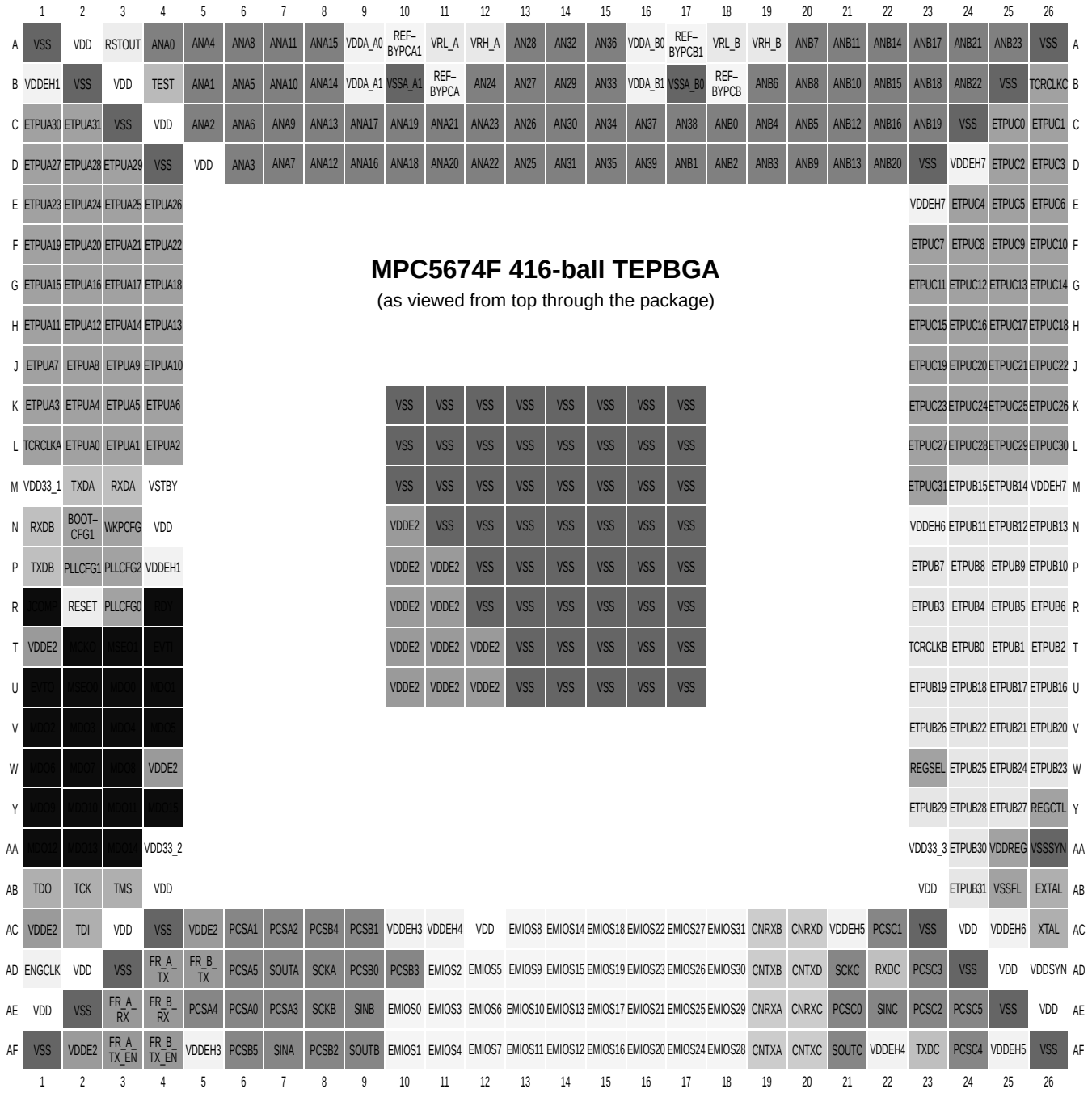

Figure 6. MPC5674F 416-ball TEPBGA (full diagram)

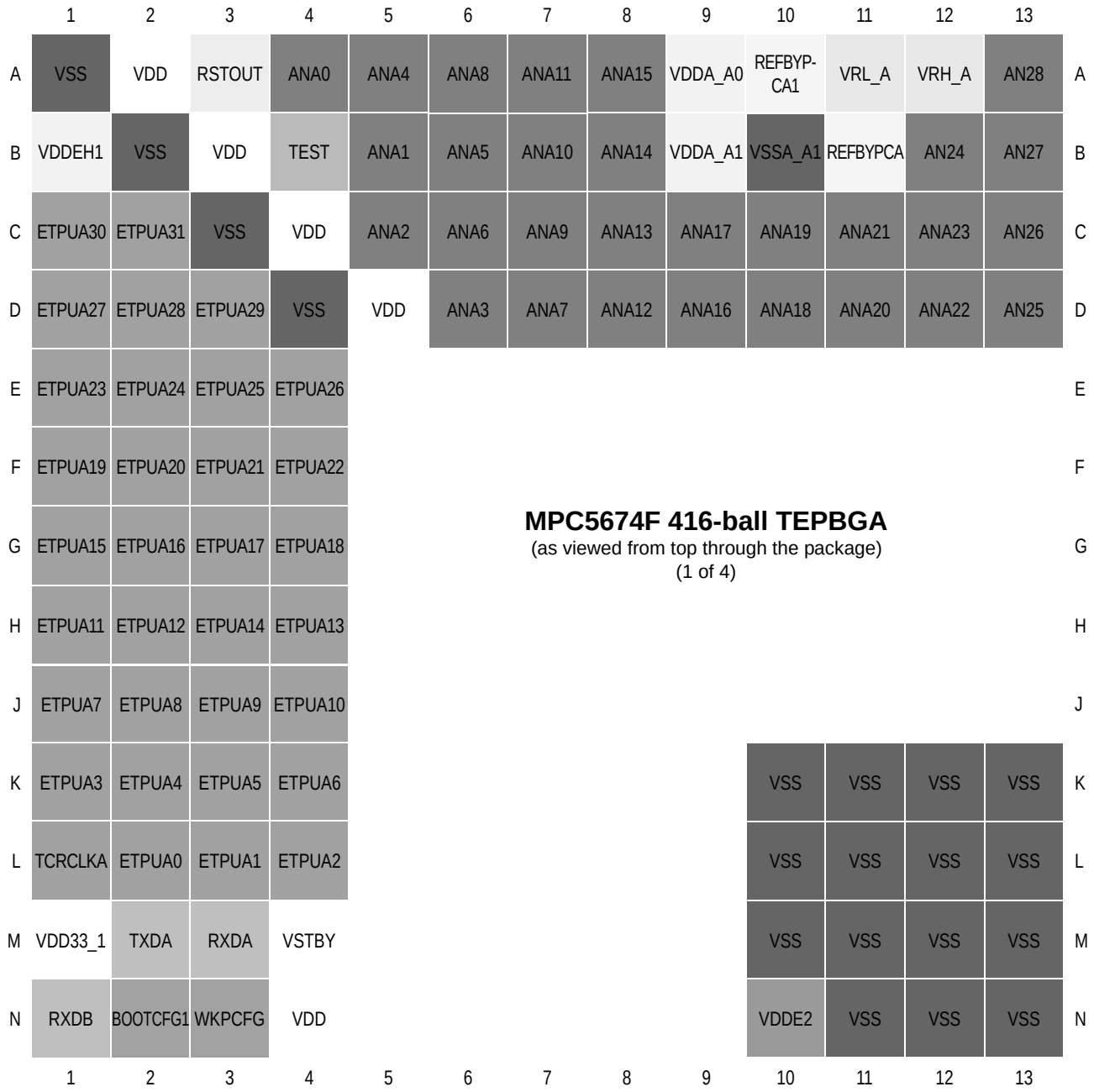

Figure 7. MPC5674F 416-ball TEPBGA (1 of 4)

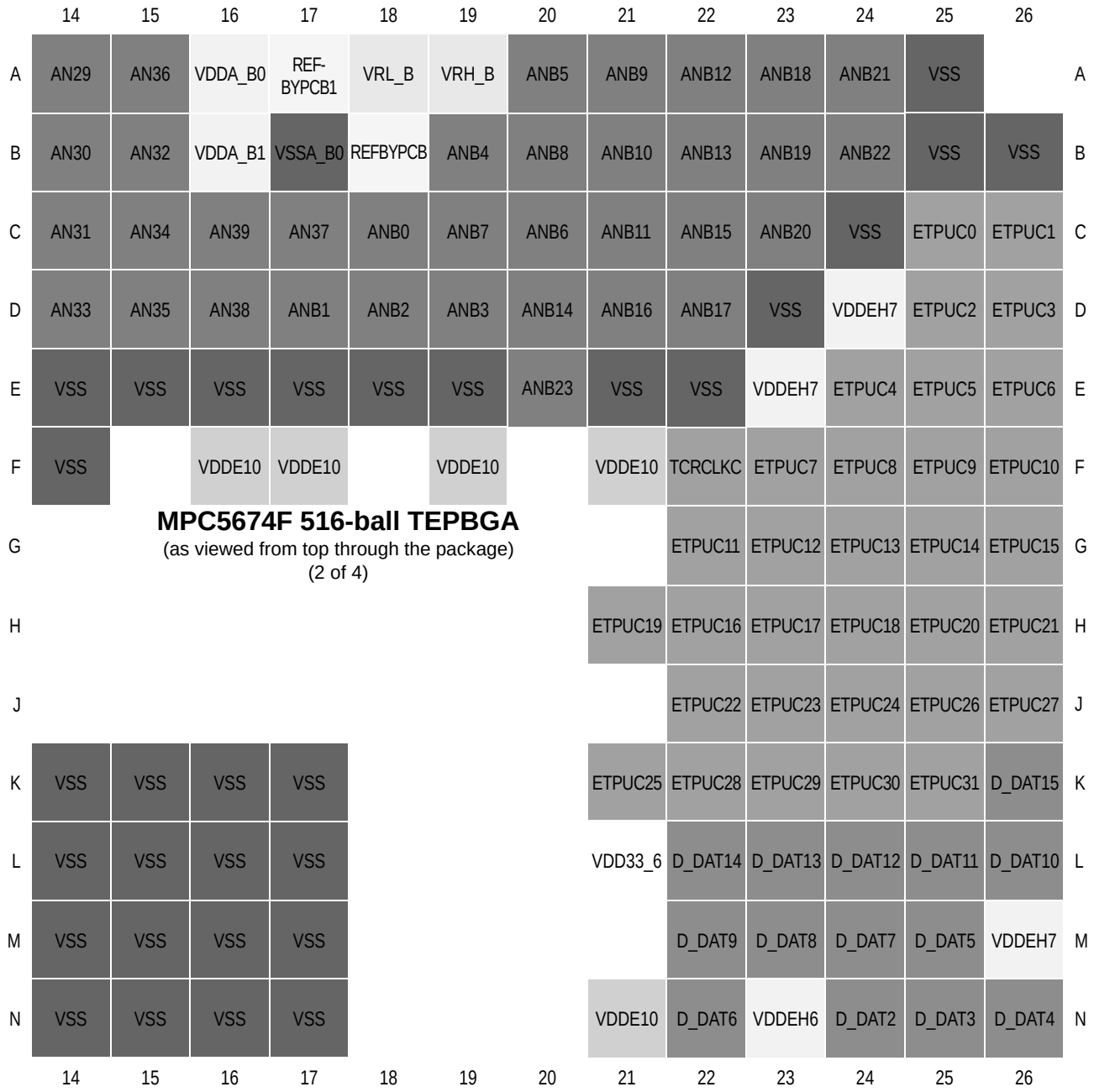

Figure 13. MPC5674F 516-ball TEPBGA (2 of 4)

3.4 Signal Properties and Muxing

See Appendix A, Signal Properties and Muxing, for a listing and description of the pin functions and properties.

6 Indicates the average thermal resistance between the die and the case top surface as measured by the cold plate method (MIL SPEC-883 Method 1012.1) with the cold plate temperature used for the case temperature.

7 Thermal characterization parameter indicating the temperature difference between package top and the junction temperature per JEDEC JESD51-2.

4.2.1 General Notes for Specifications at Maximum Junction Temperature

An estimation of the chip junction temperature, T_J, can be obtained from the equation:

$$T_J = T_A + (R_{\theta JA} * P_D) \quad \textit{Eqn. 1}$$

where:

T_A = ambient temperature for the package (^oC)

$R_{\theta JA}$ = junction to ambient thermal resistance ($^oC/W$)

P_D = power dissipation in the package (W)

The junction to ambient thermal resistance is an industry standard value that provides a quick and easy estimation of thermal performance. Unfortunately, there are two values in common usage: the value determined on a single layer board and the value obtained on a board with two planes. For packages such as the TEPBGA, these values can be different by a factor of two. Which value is closer to the application depends on the power dissipated by other components on the board. The value obtained on a single layer board is appropriate for the tightly packed printed circuit board. The value obtained on the board with the internal planes is usually appropriate if the board has low power dissipation and the components are well separated.

When a heat sink is used, the thermal resistance is expressed as the sum of a junction to case thermal resistance and a case to ambient thermal resistance:

$$R_{\theta JA} = R_{\theta JC} + R_{\theta CA} \quad \textit{Eqn. 2}$$

where:

$R_{\theta JA}$ = junction to ambient thermal resistance ($^oC/W$)

$R_{\theta JC}$ = junction to case thermal resistance ($^oC/W$)

$R_{\theta CA}$ = case to ambient thermal resistance ($^oC/W$)

$R_{\theta JC}$ is device related and cannot be influenced by the user. The user controls the thermal environment to change the case to ambient thermal resistance, $R_{\theta CA}$. For instance, the user can change the size of the heat sink, the air flow around the device, the interface material, the mounting arrangement on printed circuit board, or change the thermal dissipation on the printed circuit board surrounding the device.

To determine the junction temperature of the device in the application when heat sinks are not used, the Thermal Characterization Parameter (Ψ_{JT}) can be used to determine the junction temperature with a measurement of the temperature at the top center of the package case using the following equation:

$$T_J = T_T + (\Psi_{JT} \times P_D) \quad \textit{Eqn. 3}$$

where:

T_T = thermocouple temperature on top of the package (^oC)

Ψ_{JT} = thermal characterization parameter ($^oC/W$)

P_D = power dissipation in the package (W)

The thermal characterization parameter is measured per JESD51-2 specification using a 40 gauge type T thermocouple epoxied to the top center of the package case. The thermocouple should be positioned so that the thermocouple junction rests on the

Table 14. DC Electrical Specifications (continued)

Spec	Characteristic	Symbol	Min	Max	Unit
27	Operating Current V_{DDE}/V_{DDEH}[17] Supplies V_{DDE2} V_{DDEH1} V_{DDEH3} V_{DDEH4} V_{DDEH5} V_{DDEH6} V_{DDEH7}	 I_{DD2} I_{DD1} I_{DD3} I_{DD4} I_{DD5} I_{DD6} I_{DD7}	 — — — — — — —	 note[17]	 mA mA mA mA mA mA mA
28	Fast I/O Weak Pull Up/Down Current[18] 3.0 V–3.6 V	 I_{ACT_F}	 42	 158	 µA
29	Medium I/O Weak Pull Up/Down Current[19] 3.0 V–3.6 V 4.5 V–5.5 V	I_{ACT_S}	 15 35	 95 200	 µA µA
30	I/O Input Leakage Current[20]	I_{INACT_D}	–2.5	2.5	µA
31	DC Injection Current (per pin)	I_{IC}	–1.0	1.0	mA
32	Analog Input Current, Channel Off[21], AN[0:7], AN38, AN39 Analog Input Current, Channel Off, all other analog inputs AN[x]	I_{INACT_A}	–250 –150	250 150	nA nA
33	V_{SS} Differential Voltage	$V_{SS} - V_{SSA}$	–100	100	mV
34	Analog Reference Low Voltage	V_{RL}	V_{SSA}	V_{SSA} + 100	mV
35	V_{RL} Differential Voltage	$V_{RL} - V_{SSA}$	–100	100	mV
36	Analog Reference High Voltage	V_{RH}	V_{DDA} – 100	V_{DDA}	mV
37	V_{REF} Differential Voltage	$V_{RH} - V_{RL}$	4.75	5.25	V
38	V_{SSSYN} to V_{SS} Differential Voltage	$V_{SSSYN} - V_{SS}$	–100	100	mV
39	Operating Temperature Range—Ambient (Packaged)	T_A (T_L to T_H)	–40.0	125.0	°C
40	Slew rate on power supply pins	—	—	25	V/ms
41	Weak Pull-Up/Down Resistance[22], 200 K Option	$R_{PUPD200K}$	130	280	kΩ
42	Weak Pull-Up/Down Resistance[22], 100 K Option	$R_{PUPD100K}$	65	140	kΩ
43	Weak Pull-Up/Down Resistance[22], 5 K Option	R_{PUPD5K}	1.4	7.5	kΩ
44	Pull-Up/Down Resistance Matching Ratios[23] (100K/200K)	$R_{PUPDMTCH}$	–2.5	+2.5	%

1 Voltage overshoots during a high-to-low or low-to-high transition must not exceed 10 seconds per instance.

2 2.0 V for 10 hours cumulative time, 1.2 V +10% for time remaining.

3 Assumed with DC load.

4 5.3 V for 10 hours cumulative time, 3.3 V +10% for time remaining.

5 6.4 V for 10 hours cumulative time, 5.0 V +10% for time remaining.

6 V_{STBY} below 0.95 V the RAM will not retain states, but will be operational. V_{STBY} can be 0 V when bypass standby mode.

7 Regulator is functional with derated performance, with supply voltage down to 4.0 V for system with V_{DDREG} = 4.5 V (min).

8 2.7 V minimum operating voltage allowed during vehicle crank for system with V_{DDREG} = 3.0 V (min). Normal operating voltage should be either V_{DDREG} = 3.0 V (min) or 4.5 V (min) depending on the user regulation voltage system selected.

9 Required to be supplied when 3.3 V regulator is disabled. See Section 4.5, “PMC/POR/LVI Electrical Specifications.”

4.7.3 LVDS Pad Specifications

LVDS pads are implemented to support the MSC (Microsecond Channel) protocol, which is an enhanced feature of the DSPI module.

Table 17. DSPI LVDS pad specification

#	Characteristic	Symbol	Condition	Min. Value	Typ. Value	Max. Value	Unit
Data Rate							
1	Data Frequency	$f_{LVDSCLK}$	—	—	50	—	MHz
Driver Specs							
2	Differential output voltage	V_{OD}	SRC=0b00 or 0b11	150	—	400	mV
			SRC=0b01	90	—	320	
			SRC=0b10	160	—	480	
3	Common mode voltage (LVDS), VOS	V_{OS}	—	1.06	1.2	1.39	V
4	Rise/Fall time	T_R/T_F	—	—	2	—	ns
5	Propagation delay (Low to High)	T_{PLH}	—	—	4	—	ns
6	Propagation delay (High to Low)	T_{PHL}	—	—	4	—	ns
7	Delay (H/L), sync Mode	t_{PDSYNC}	—	—	4	—	ns
8	Delay, Z to Normal (High/Low)	T_{DZ}	—	—	500	—	ns
9	Diff Skew ltphla-tplhbl or ltplhb-tphlal	T_{SKEW}	—	—	—	0.5	ns
Termination							
10	Trans. Line (differential Zo)	—	—	95	100	105	ohms
11	Temperature	—	—	–40	—	150	°C

4.8 Oscillator and FMPLL Electrical Characteristics

Table 18. FMPLL Electrical Specifications[1]

(V_{DDSYN} = 3.0 V to 3.6 V, V_{SS} = V_{SSSYN} = 0 V, T_A = T_L to T_H)

Spec	Characteristic	Symbol	Min	Max	Unit
1	PLL Reference Frequency Range[2] (Normal Mode) Crystal Reference (PLLCFG2 = 0b0) Crystal Reference (PLLCFG2 = 0b1) External Reference (PLLCFG2 = 0b0) External Reference (PLLCFG2 = 0b1)	 $f_{ref\_crystal}$ $f_{ref\_crystal}$ f_{ref_ext} f_{ref_ext}	 8 16 8 16	 20 40[3] 20 40	MHz
2	Loss of Reference Frequency[4]	f_{LOR}	100	1000	kHz
3	Self Clocked Mode Frequency[5]	f_{SCM}	4	16	MHz
4	PLL Lock Time[6]	t_{LPLL}	—	< 400	µs

Table 20. eQADC Conversion Specifications (Operating) (continued)

Spec	Characteristic	Symbol	Min	Max	Unit
9	Offset Error without Calibration	OFFNC	0[4]	100[4]	LSB
10	Offset Error with Calibration	OFFWC	–4[4]	4[4]	LSB
11	Full Scale Gain Error without Calibration	GAINNC	–120[4]	0[4]	LSB
12	Full Scale Gain Error with Calibration	GAINWC	–4[4,6]	4[4,6]	LSB
13	Non-Disruptive Input Injection Current [7, 8, 9, 10]	I_{INJ}	–3	3	mA
14	Incremental Error due to injection current[11, 12]	E_{INJ}	–4[4]	4[4]	Counts
15	TUE value at 8 MHz [13, 14] (with calibration)	TUE8	–4[4,6]	4[4,6]	Counts
16	TUE value at 16 MHz [13, 14] (with calibration)	TUE16	–8	8	Counts
17	Maximum differential voltage[15] (DANx+ - DANx-) or (DANx- - DANx+) PREGAIN set to 1X setting PREGAIN set to 2X setting PREGAIN set to 4X setting	 $DIFF_{max}$ $DIFF_{max2}$ $DIFF_{max4}$	 — — —	 $(V_{RH} – V_{RL})/2$ $(V_{RH} – V_{RL})/4$ $(V_{RH} - V_{RL})/8$	 V V V
18	Differential input Common mode voltage[15] (DANx- + DANx+)/2	$DIFF_{cmv}$	$(V_{RH} – V_{RL})/2$ – 5%	$(V_{RH} – V_{RL})/2$ + 5%	V

1 Stop mode recovery time is the time from the setting of either of the enable bits in the ADC Control Register to the time that the ADC is ready to perform conversions. Delay from power up to full accuracy = 8 ms.

2 At $V_{RH} – V_{RL}$ = 5.12 V, one count = 1.25 mV without using pregain.

3 INL and DNL are tested from V_{RL} + 50 LSB to V_{RH} – 50 LSB. The eQADC is guaranteed to be monotonic at 10 bit accuracy (12 bit resolution selected).

4 New design target. Actual specification will change following characterization. Margin for manufacturing has not been fully included.

5 At $V_{RH} – V_{RL}$ = 5.12 V, one LSB = 1.25 mV.

6 The value is valid at 8 MHz, it is ±8 counts at 16 Mhz.

7 Below disruptive current conditions, the channel being stressed has conversion values of $3FF for analog inputs greater than V_{RH} and $000 for values less than V_{RL}. Other channels are not affected by non-disruptive conditions.

8 Exceeding limit may cause conversion error on stressed channels and on unstressed channels. Transitions within the limit do not affect device reliability or cause permanent damage.

9 Input must be current limited to the value specified. To determine the value of the required current-limiting resistor, calculate resistance values using $V_{POSCLAMP} = V_{DDA}$ + 0.5 V and $V_{NEGCLAMP}$ = –0.3 V, then use the larger of the calculated values.

10 Condition applies to two adjacent pins at injection limits.

11 Performance expected with production silicon.

12 All channels have same 10 kΩ < Rs < 100 kΩ Channel under test has Rs = 10 kΩ, I_{INJ}=I_{INJMAX},I_{INJMIN}.

13 The TUE specification is always less than the sum of the INL, DNL, offset, and gain errors due to cancelling errors.

14 TUE does not apply to differential conversions.

15 Voltages between VRL and VRH will not cause damage to the pins. However, they may not be converted accurately if the differential voltage is above the maximum differential voltage. In addition, conversion errors may occur if the common mode voltage of the differential signal violates the Differential Input common mode voltage specification.

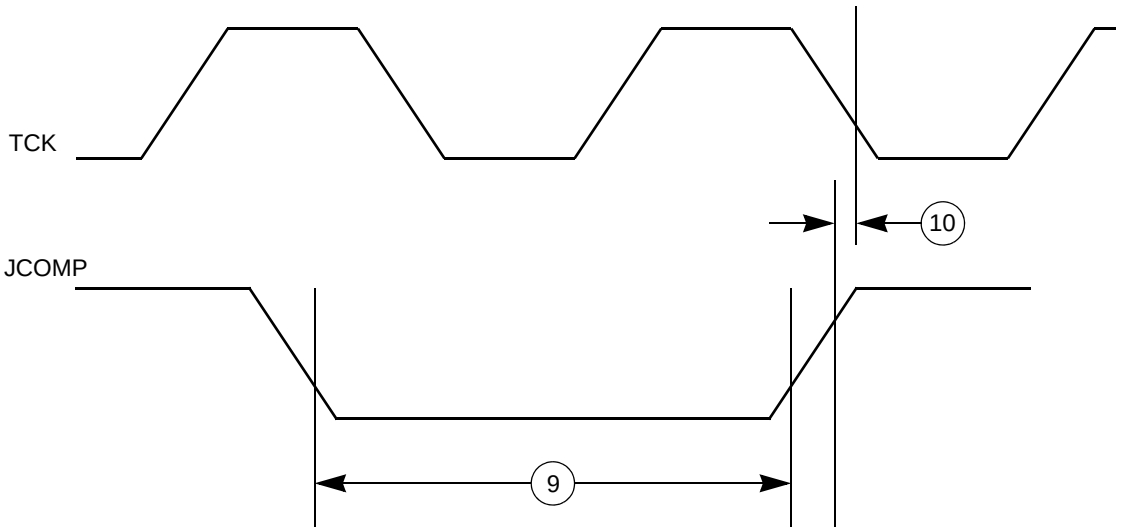

Figure 23. JTAG JCOMP Timing

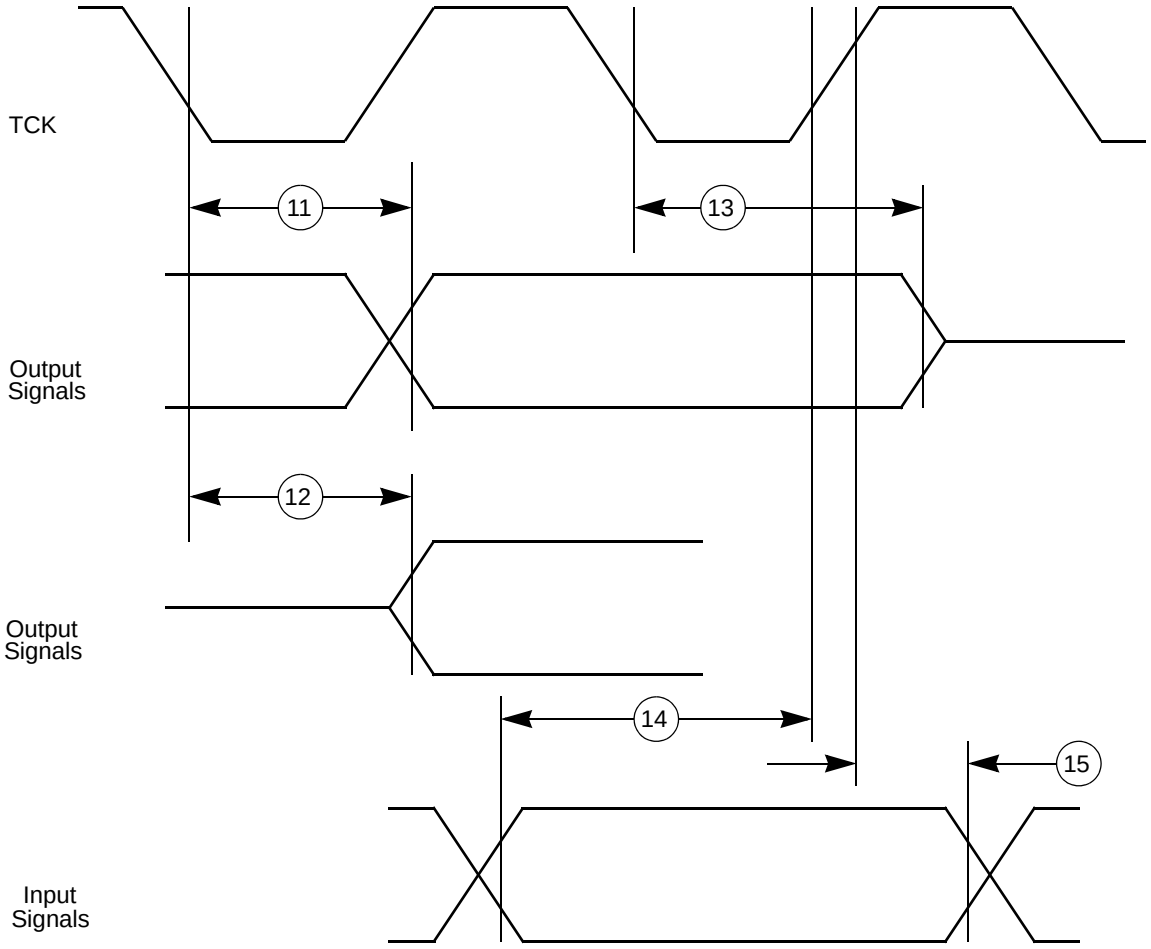

Figure 24. JTAG Boundary Scan Timing

Table 36. Bus Operation Timing [1] (continued)

Spec	Characteristic	Symbol	66 MHz (Ext. Bus Freq)[2 3]		Unit	Notes
			Min	Max		
7	Input Signal Valid to D_CLKOUT Posedge (Setup Time) D_ADD[9:30] D_DAT[0:15] D_RD_WR D_TA D_TS	t_{CIS}	5.0/4.5	—	ns	Input setup time selectable via SIU_ECCR[EBTS] bit: EBTS = 0; 5.0ns EBTS = 1; 4.5ns
8	D_CLKOUT Posedge to Input Signal Invalid (Hold Time) D_ADD[9:30] D_DAT[0:15] D_RD_WR D_TA D_TS	t_{CIH}	1.0	—	ns	
9	D_ALE Pulse Width	t_{APW}	6.5	—	ns	The timing is for Asynchronous external memory system.
10	D_ALE Negated to Address Invalid	t_{AAI}	2.0/1.0 [5]	—	ns	The timing is for Asynchronous external memory system. ALE is measured at 50% of VDDE.

1 EBI timing specified at V_{DD} = 1.08 V to 1.32 V, V_{DDE} = 3.0 V to 3.6 V, V_{DD33} and V_{DDSYN} = 3.0 V to 3.6 V, $T_A = T_L$ to T_H, and C_L = 30 pF with DSC = 0b10.

2 Speed is the nominal maximum frequency. Max speed is the maximum speed allowed including frequency modulation (FM). 270 MHz parts allow for 264 MHz system clock + 2% FM.

3 Depending on the internal bus speed, set the SIU_ECCR[EBDF] bits correctly not to exceed maximum external bus frequency. The maximum external bus frequency is 66 MHz.

4 Refer to Fast pad timing in Table 31 and Table 32.

5 ALE hold time spec is temperature dependant. 1.0 ns spec applies for temperature range -40 to 0 °C. 2.0 ns spec applies to temperatures > 0 °C. This spec has no dependency on SIU_ECCR[EBTS] bit.

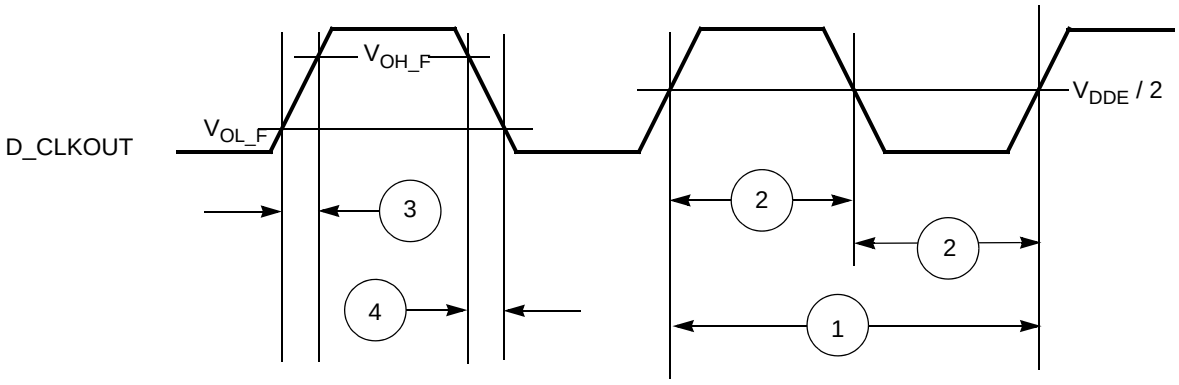

Figure 27. D_CLKOUT Timing

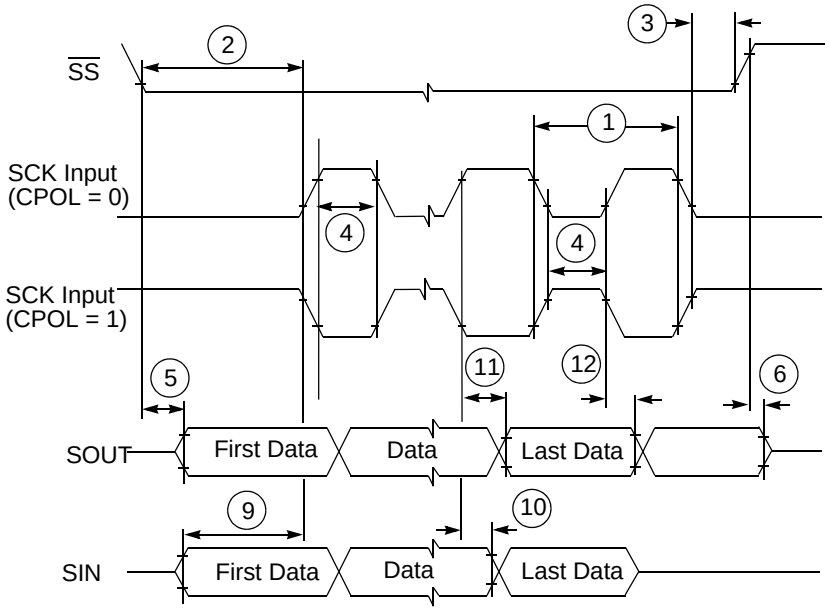

Figure 40. DSPI Modified Transfer Format Timing — Slave, CPHA = 0

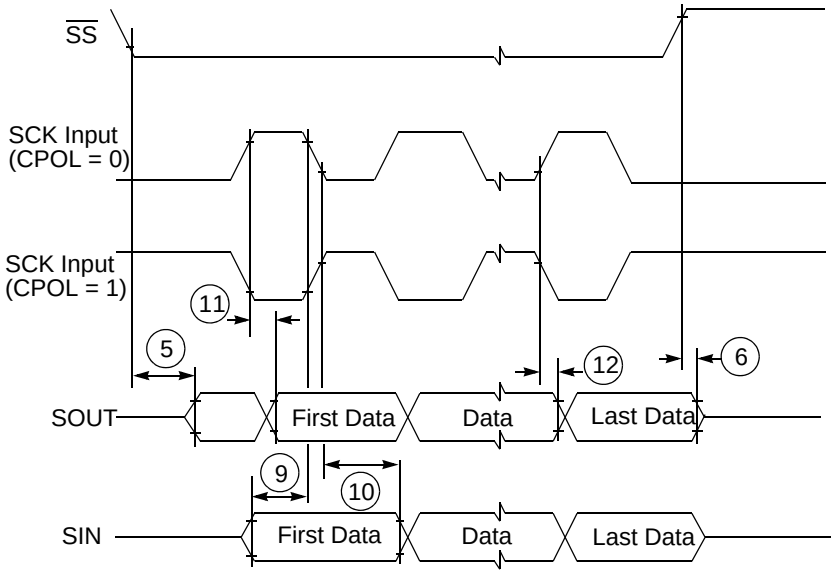

Figure 41. DSPI Modified Transfer Format Timing — Slave, CPHA = 1

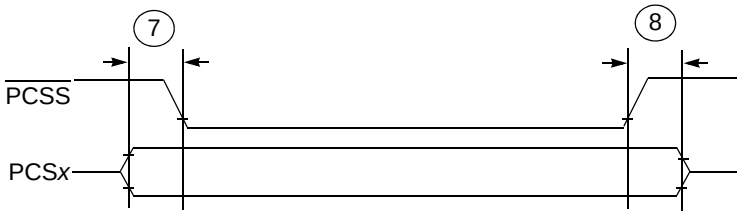

Figure 42. DSPI PCS Strobe ($\overline{\text{PCSS}}$) Timing

5.1 324-Pin Package

The package drawings of the 324-pin TEPBGA package are shown in Figure 43 and Figure 44.

Figure 43. 324 TEPBGA Package (1 of 2)

Table 43. Signal Properties and Muxing Summary (continued)

GPIO/PCR[1]	Signal Name[2]	P/A/G[3]	Function[4]	Function Summary	Direction	Pad Type[5]	Voltage[6]	State during RESET[7]	State after RESET[8]	Package Location		
										324	416	516
143	ETPUA29_PCSC2_ GPIO143	P	ETPUA29	eTPU A channel	I/O	MH	V_{DDEH1}	—/WKPCFG	—/WKPCFG	—	D3	D3
		A1	PCSC2	DSPI C peripheral chip select	O							
		A2	—	—	—							
		G	GPIO143	GPIO	I/O							
144	ETPUA30_PCSC3_ GPIO144	P	ETPUA30	eTPU A channel	I/O	MH	V_{DDEH1}	—/WKPCFG	—/WKPCFG	E4	C1	C1
		A1	PCSC3	DSPI C peripheral chip select	O							
		A2	—	—	—							
		G	GPIO144	GPIO	I/O							
145	ETPUA31_PCSC4_ GPIO145	P	ETPUA31	eTPU A channel	I/O	MH	V_{DDEH1}	—/WKPCFG	—/WKPCFG	D3	C2	C2
		A1	PCSC4	DSPI C peripheral chip select	O							
		A2	—	—	—							
		G	GPIO145	GPIO	I/O							
eTPU_B												
146	TCRCLKB_IRQ6_ GPIO146	P	TCRCLKB	eTPU B TCR clock	I	MH	V_{DDEH6}	—/Up	—/Up	P19	T23	V25
		A1	IRQ6	External interrupt request	I							
		A2	—	—	—							
		G	GPIO146	GPIO	I/O							
147	ETPUB0_ETPUB16_ GPIO147	P	ETPUB0	eTPU B channel	I/O	MH	V_{DDEH6}	—/WKPCFG	—/WKPCFG	N19	T24	V26
		A1	ETPUB16	eTPU B channel (output only)	O							
		A2	—	—	—							
		G	GPIO147	GPIO	I/O							
148	ETPUB1_ETPUB17_ GPIO148	P	ETPUB1	eTPU B channel	I/O	MH	V_{DDEH6}	—/WKPCFG	—/WKPCFG	R19	T25	U22
		A1	ETPUB17	eTPU B channel (output only)	O							
		A2	—	—	—							
		G	GPIO148	GPIO	I/O							

Table 43. Signal Properties and Muxing Summary (continued)

GPIO/PCR[1]	Signal Name[2]	P/A/G[3]	Function[4]	Function Summary	Direction	Pad Type[5]	Voltage[6]	State during RESET[7]	State after RESET[8]	Package Location		
										324	416	516
433	EMIOS27_PCSB3_ GPIO433	P	EMIOS27	eMIOS channel	I/O	MH	V_{DDEH4}	—/WKPCFG	—/WKPCFG	W14	AC17	AD18
		A1	PCSB3	DSPI B peripheral chip select	O							
		A2	—	—	—							
		G	GPIO433	GPIO	I/O							
434	EMIOS28_PCSC0_ GPIO434	P	EMIOS28	eMIOS channel	I/O	MH	V_{DDEH4}	—/WKPCFG	—/WKPCFG	AA16	AF18	AC18
		A1	PCSC0	DSPI C peripheral chip select	I/O							
		A2	—	—	—							
		G	GPIO434	GPIO	I/O							
435	EMIOS29_PCSC1_ GPIO435	P	EMIOS29	eMIOS channel	I/O	MH	V_{DDEH4}	—/WKPCFG	—/WKPCFG	AA17	AE18	AB17
		A1	PCSC1	DSPI C peripheral chip select	O							
		A2	—	—	—							
		G	GPIO435	GPIO	I/O							
436	EMIOS30_PCSC2_ GPIO436	P	EMIOS30	eMIOS channel	I/O	MH	V_{DDEH4}	—/WKPCFG	—/WKPCFG	Y17	AD18	AF19
		A1	PCSC2	DSPI C peripheral chip select	O							
		A2	—	—	—							
		G	GPIO436	GPIO	I/O							
437	EMIOS31_PCSC5_ GPIO437	P	EMIOS31	eMIOS channel	I/O	MH	V_{DDEH4}	—/WKPCFG	—/WKPCFG	W15	AC18	AA17
		A1	PCSC5	DSPI C peripheral chip select	O							
		A2	—	—	—							
		G	GPIO437	GPIO	I/O							
eQADC												
—	ANA0	P	ANA0[10]	eQADC A analog input	I	AE/up-down	V_{DDA_A1}	ANA0	ANA0	A4	A4	A4
—	ANA1	P	ANA1[10]	eQADC A analog input	I	AE/up-down	V_{DDA_A1}	ANA1	ANA1	A5	B5	B5
—	ANA2	P	ANA2[10]	eQADC A analog input	I	AE/up-down	V_{DDA_A1}	ANA2	ANA2	B5	C5	C5

Table 43. Signal Properties and Muxing Summary (continued)

GPIO/PCR[1]	Signal Name[2]	P/A/G[3]	Function[4]	Function Summary	Direction	Pad Type[5]	Voltage[6]	State during RESET[7]	State after RESET[8]	Package Location		
										324	416	516
—	ANB9	P	ANB9	eQADC B analog input	I	AE	V_{DDA_B0}	ANB9	ANB9	C14	D20	A21
—	ANB10	P	ANB10	eQADC B analog input	I	AE	V_{DDA_B0}	ANB10	ANB10	C13	B21	B21
—	ANB11	P	ANB11	eQADC B analog input	I	AE	V_{DDA_B0}	ANB11	ANB11	C15	A21	C21
—	ANB12	P	ANB12	eQADC B analog input	I	AE	V_{DDA_B0}	ANB12	ANB12	C16	C21	A22
—	ANB13	P	ANB13	eQADC B analog input	I	AE	V_{DDA_B0}	ANB13	ANB13	D14	D21	B22
—	ANB14	P	ANB14	eQADC B analog input	I	AE	V_{DDA_B0}	ANB14	ANB14	C17	A22	D20
—	ANB15	P	ANB15	eQADC B analog input	I	AE	V_{DDA_B0}	ANB15	ANB15	D15	B22	C22
—	ANB16	P	ANB16	eQADC B analog input	I	AE	V_{DDA_B0}	ANB16	ANB16	C18	C22	D21
—	ANB17	P	ANB17	eQADC B analog input	I	AE	V_{DDA_B0}	ANB17	ANB17	D16	A23	D22
—	ANB18	P	ANB18	eQADC B analog input	I	AE	V_{DDA_B0}	ANB18	ANB18	D17	B23	A23
—	ANB19	P	ANB19	eQADC B analog input	I	AE	V_{DDA_B0}	ANB19	ANB19	B19	C23	B23
—	ANB20	P	ANB20	eQADC B analog input	I	AE	V_{DDA_B0}	ANB20	ANB20	C19	D22	C23
—	ANB21	P	ANB21	eQADC B analog input	I	AE	V_{DDA_B0}	ANB21	ANB21	D18	A24	A24
—	ANB22	P	ANB22	eQADC B analog input	I	AE	V_{DDA_B0}	ANB22	ANB22	A21	B24	B24
—	ANB23	P	ANB23	eQADC B analog input	I	AE	V_{DDA_B0}	ANB23	ANB23	B20	A25	E20
—	VRH_A	P	VRH_A	ADC A Voltage reference high	I	VDDINT	V_{RH_A}	VRH_A	VRH_A	A10	A12	A12
—	VRL_A	P	VRL_A	ADC A Voltage reference low	I	VSSINT	V_{RL_A}	VRL_A	VRL_A	A11	A11	A11
—	VRH_B	P	VRH_B	ADC B Voltage reference high	I	VDDINT	V_{RH_B}	VRH_B	VRH_B	A16	A19	A19
—	VRL_B	P	VRL_B	ADC B Voltage reference low	I	VSSINT	V_{RL_B}	VRL_B	VRL_B	A15	A18	A18
—	REFBYPCB	P	REFBYPCB	ADC B Reference bypass capacitor	I	AE	V_{DDA_B0}	REFBYPCB	REFBYPCB	B12	B18	B18
—	REFBYPCA	P	REFBYPCA	ADC A Reference bypass capacitor	I	AE	V_{DDA_A1}	REFBYPCA	REFBYPCA	B11	B11	B11
—	VDDA_A0	P	VDDA_A	Internal logic supply input	I	VDDE	V_{DDA_A0}	VDDA_A0	VDDA_A0	A9	A9	A9
—	VDDA_A1	P	VDDA_A	Internal logic supply input	I	VDDE	V_{DDA_A1}	VDDA_A1	VDDA_A1	B9	B9	B9
—	REFBYPCA1	P	REFBYPCA1	ADC A Reference bypass capacitor	I	AE	V_{DDA_A1}	REFBYPCA1	REFBYPCA1	A12	A10	A10
—	VSSA_A1	P	VSSA_A	Ground	I	VSSE	V_{SSA_A1}	VSSA_A1	VSSA_A1	B10	B10	B10
—	VDDA_B0	P	VDDA_B	Internal logic supply input	I	VDDE	V_{DDA_B0}	VDDA_B0	VDDA_B0	A13	A16	A16
—	VDDA_B1	P	VDDA_B	Internal logic supply input	I	VDDE	V_{DDA_B1}	VDDA_B1	VDDA_B1	B13	B16	B16

Table 43. Signal Properties and Muxing Summary (continued)

GPIO/PCR[1]	Signal Name[2]	P/A/G[3]	Function[4]	Function Summary	Direction	Pad Type[5]	Voltage[6]	State during RESET[7]	State after RESET[8]	Package Location		
										324	416	516
253	FR_B_TX_EN_ GPIO253	P	FR_B_TX_EN	FlexRay B transfer enable	O	FS	V_{DDE2}	—/Up (–/– for Rev.1 of the device)	—/Up (–/– for Rev.1 of the device)	AB5	AF4	AF4
		A1	—	—	—							
		A2	—	—	—							
		G	GPIO253	GPIO	I/O							
FlexCAN												
83	CNTXA_TXDA_ GPIO83	P	CNTXA	FlexCAN A transmit	O	MH	V_{DDEH4}	—/Up	—/Up	AB17	AF19	AE19
		A1	TXDA	eSCI A transmit	O							
		A2	—	—	—							
		G	GPIO83	GPIO	I/O							
84	CNRXA_RXDA_ GPIO84	P	CNRXA	FlexCAN A receive	I	MH	V_{DDEH4}	—/Up	—/Up	AA18	AE19	AD19
		A1	RXDA	eSCI A receive	I							
		A2	—	—	—							
		G	GPIO84	GPIO	I/O							
85	CNTXB_PCSC3_ GPIO85	P	CNTXB	FlexCAN B transmit	O	MH	V_{DDEH4}	—/Up	—/Up	Y18	AD19	AC19
		A1	PCSC3	DSPI C peripheral chip select	O							
		A2	—	—	—							
		G	GPIO85	GPIO	I/O							
86	CNRXB_PCSC4_ GPIO86	P	CNRXB	FlexCAN B receive	I	MH	V_{DDEH4}	—/Up	—/Up	W18	AC19	AA19
		A1	PCSC4	DSPI C peripheral chip select	O							
		A2	—	—	—							
		G	GPIO86	GPIO	I/O							
87	CNTXC_PCSD3_ GPIO87	P	CNTXC	FlexCAN C transmit	O	MH	V_{DDEH4}	—/Up	—/Up	W16	AF20	AF20
		A1	PCSD3	DSPI D peripheral chip select	O							
		A2	—	—	—							
		G	GPIO87	GPIO	I/O							

Table 43. Signal Properties and Muxing Summary (continued)

GPIO/PCR[1]	Signal Name[2]	P/A/G[3]	Function[4]	Function Summary	Direction	Pad Type[5]	Voltage[6]	State during RESET[7]	State after RESET[8]	Package Location		
										324	416	516
92	RXDB_PCSD5_ GPIO92	P	RXDB	eSCI B receive	I	MH	V_{DDEH1}	—/Up	—/Up	—	N1	L5
		A1	PCSD5	DSPI D peripheral chip select	O							
		A2	—	—	—							
		G	GPIO92	GPIO	I/O							
244	TXDC_ETRIG0_ GPIO244	P	TXDC	eSCI C transmit	O	MH	V_{DDEH4}	—/Up	—/Up	—	AF23	AF23
		A1	ETRIG0	eQADC trigger input	I							
		A2	—	—	—							
		G	GPIO244	GPIO	I/O							
245	RXDC_ GPIO245	P	RXDC	eSCI C receive	I	MH	V_{DDEH5}	—/Up	—/Up	—	AD22	AD22
		A1	—	—	—							
		A2	—	—	—							
		G	GPIO245	GPIO	I/O							
DSPI												
93	SCKA_PCSC1_ GPIO93	P	SCKA	DSPI A clock	I/O	MH	V_{DDEH3}	—/Up	—/Up	Y7	AD8	AB8
		A1	PCSC1	DSPI C peripheral chip select	O							
		A2	—	—	—							
		G	GPIO93	GPIO	I/O							
94	SINA_PCSC2_ GPIO94	P	SINA	DSPI A data input	I	MH	V_{DDEH3}	—/Up	—/Up	AA7	AF7	AE7
		A1	PCSC2	DSPI C peripheral chip select	O							
		A2	—	—	—							
		G	GPIO94	GPIO	I/O							
95	SOUTA_PCSC5_ GPIO95	P	SOUTA	DSPI A data output	O	MH	V_{DDEH3}	—/Up	—/Up	AB7	AD7	AC7
		A1	PCSC5	DSPI C peripheral chip select	O							
		A2	—	—	—							
		G	GPIO95	GPIO	I/O							

Table 43. Signal Properties and Muxing Summary (continued)

GPIO/PCR[1]	Signal Name[2]	P/A/G[3]	Function[4]	Function Summary	Direction	Pad Type[5]	Voltage[6]	State during RESET[7]	State after RESET[8]	Package Location		
										324	416	516
283	D_ADD_DAT5_ GPIO283	P	D_ADD_DAT5	EBI data only in non-mux mode. Address and data in mux mode.	I/O	F	V_{DDE10}	—/Up	—/Up	—	—	M25
		A1	—	—	—							
		A2	—	—	—							
		G	GPIO283	GPIO	I/O							
284	D_ADD_DAT6_ GPIO284	P	D_ADD_DAT6	EBI data only in non-mux mode. Address and data in mux mode.	I/O	F	V_{DDE10}	—/Up	—/Up	—	—	N22
		A1	—	—	—							
		A2	—	—	—							
		G	GPIO284	GPIO	I/O							
285	D_ADD_DAT7_ GPIO285	P	D_ADD_DAT7	EBI data only in non-mux mode. Address and data in mux mode.	I/O	F	V_{DDE10}	—/Up	—/Up	—	—	M24
		A1	—	—	—							
		A2	—	—	—							
		G	GPIO285	GPIO	I/O							
286	D_ADD_DAT8_ GPIO286	P	D_ADD_DAT8	EBI data only in non-mux mode. Address and data in mux mode.	I/O	F	V_{DDE10}	—/Up	—/Up	—	—	M23
		A1	—	—	—							
		A2	—	—	—							
		G	GPIO286	GPIO	I/O							
287	D_ADD_DAT9_ GPIO287	P	D_ADD_DAT9	EBI data only in non-mux mode. Address and data in mux mode.	I/O	F	V_{DDE10}	—/Up	—/Up	—	—	M22
		A1	—	—	—							
		A2	—	—	—							
		G	GPIO287	GPIO	I/O							

Table 43. Signal Properties and Muxing Summary (continued)

GPIO/PCR[1]	Signal Name[2]	P/A/G[3]	Function[4]	Function Summary	Direction	Pad Type[5]	Voltage[6]	State during RESET[7]	State after RESET[8]	Package Location		
										324	416	516
293	D_ADD_DAT15_GPIO293	P	D_ADD_DAT15	EBI data only in non-mux mode. Address and data in mux mode.	I/O	F	V_{DDE10}	—/Up	—/Up	—	—	K26
		A1	—	—	—							
		A2	—	—	—							
		G	GPIO293	GPIO	I/O							
294	D_RD_WR_GPIO294	P	D_RD_WR	EBI read/write	O	F	V_{DDE10}	—/Up	—/Up	—	—	R26
		A1	—	—	—							
		A2	—	—	—							
		G	GPIO294	GPIO	I/O							
295	D_WE0_GPIO295	P	D_WE0	EBI write enable	O	F	V_{DDE8}	—/Up	—/Up	—	—	N1
		A1	—	—	—							
		A2	—	—	—							
		G	GPIO295	GPIO	I/O							
296	D_WE1_GPIO296	P	D_WE1	EBI write enable	O	F	V_{DDE8}	—/Up	—/Up	—	—	P5
		A1	—	—	—							
		A2	—	—	—							
		G	GPIO296	GPIO	I/O							
297	D_OE_GPIO297	P	D_OE	EBI output enable	O	F	V_{DDE10}	—/Up	—/Up	—	—	P23
		A1	—	—	—							
		A2	—	—	—							
		G	GPIO297	GPIO	I/O							
298	D_TS_GPIO298	P	D_TS	EBI transfer start	O	F	V_{DDE9}	—/Up	—/Up	—	—	AE9
		A1	—	—	—							
		A2	—	—	—							
		G	GPIO298	GPIO	I/O							

Table 47. Revision History (continued)

Revision (Date)	Description of changes
4 (cont)	“Temperature Sensor Electrical Specifications” table: Changed spec #2 to have one temperature range (-40 - 150 C) and changed spec value from ±1.0 to ±10.0 C.
	“eQADC Conversion Specifications (Operating)” table: Changed spec #13 (non-disruptive injection current) values from ±1 to ±3.
	"IPCLKDIV Settings" table, removed footnote "eMIOS and DMA are not considered peripherals here."
5 (Feb-2011)	Note 4 in Maximum Ratings updated from 2.0 V to 1.65 V. Changed I/O Supply Voltage spec in DC Electrical specs, Spec 2, from 1.62 V min to 3.0 V min. Changed the APC=RWSC value in line 1 of PFCPR1 Settings vs. Frequency of Operation table from 0b011 to 0b100 Changed note 1 for Pad AC Specifications table from Vdde = 1.62 V to 1.98 V to read Vdde = 3.0 V to 3.6 V Changed note 6 for Signal Properties and Muxing Summary table by removing the voltage range 1.8 V - 3.3 V to have 3.3 V instead of the range. Spec 2 in Table 9 “ESD Ratings“ the spec for “ESD for Charged Device Model (CDM)” changed to 250 V (other) from 500 V (other) Removed voltage ranges 1.62-1.98 V and 2.25-2.75 V from spec 28 in Table 14
6 (Feb-2011)	Same content as for Rev. 5
7 (Mar-2011)	Added entry for Rev. 6 and Rev. 7 to this table to fix a revision-numbering issue.
8 (Jun-2011)	Added the following footnotes to the “Signal Properties and Muxing Summary” table: • Footnote 10, for the ANA[0:7] signals, “During and just after POR negates, internal pull resistors can be enabled, resulting in as much as 4 mA of current draw. The pull resistors are disabled when the system clock propagates through the device.” • Footnote 15, for MDO[0:15] and MSEO[0:1] signals, “Do not connect pin directly to a power supply or ground.”
	Changed min and max values of ID 1 “Nominal bandgap reference voltage“ in Table 11 (PMC Electrical Specifications) to 0.608 V min and 0.632 V max. Changed min and max values of Spec 2 “ADC Bandgap” in Table 23 (ADC Band Gap Reference/LVI Electrical Specifications) to 1.171 V min and 1.269 V max. Changed Spec 3 of Table 26 (Flash EEPROM Module Life) from 'Minimum Data Retention at 25 °C ambient temperature' to 'Minimum Data Retention at 85 °C ambient temperature'
	Added Spec 41, 42, 43 and 44 to the “DC Electrical Specifications” table Added Note 25 to the “DC Electrical Specifications” table for Spec 41, 42 and 43 Added Note 26 to the “DC Electrical Specifications” for Spec 44 Added Spec 17 to the “eQADC Conversion Specifications (Operating)” table. Added Spec 18 to the “eQADC Conversion Specifications (Operating)” table. Added Note 15 to the “eQADC Conversion Specifications (Operating)” table for Spec 17 and 18.